

isc Silicon NPN Power Transistor

2SC5480

**DESCRIPTION**

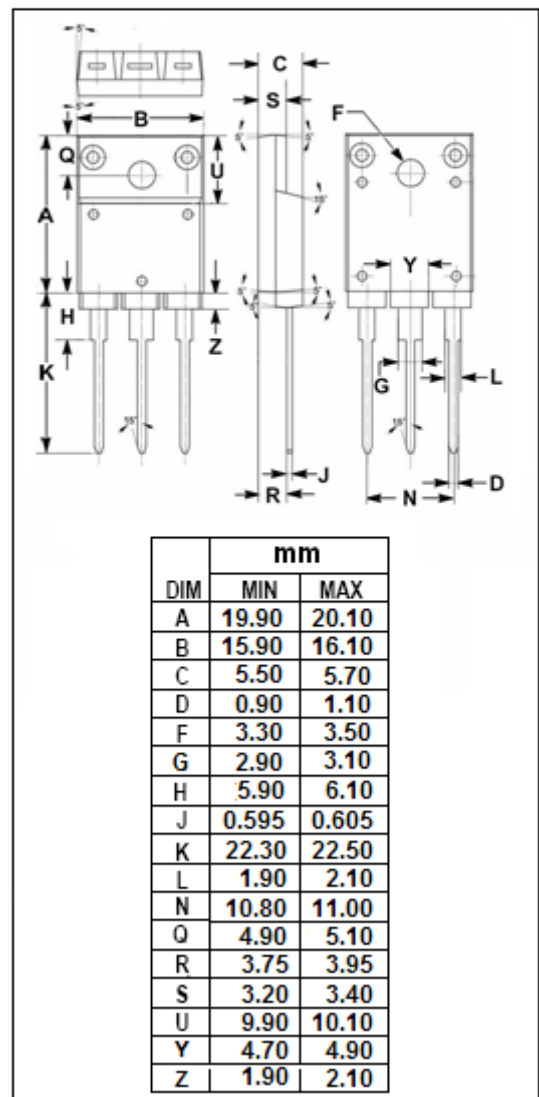
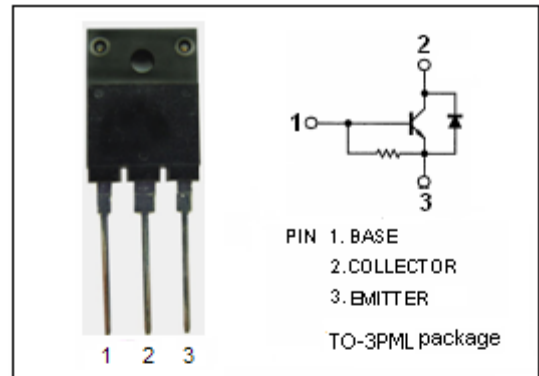
- High Breakdown Voltage-  
:  $V_{CBO} = 1500V$  (Min)
- High Switching Speed
- Built-in Damper Diode

**APPLICATIONS**

- Designed for horizontal deflection output stage applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CES}$	Collector-Emitter Voltage	1500	V
$V_{EBO}$	Emitter-Base Voltage	5	V
$I_{C(peak)}$	Collector Current-Peak	14	A
$I_{C(surge)}$	Collector Current-Surge	28	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ C$	50	W
$T_J$	Junction Temperature	150	$^\circ C$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ C$



**isc Silicon NPN Power Transistor****2SC5480****ELECTRICAL CHARACTERISTICS****T<sub>C</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 500mA; I <sub>C</sub> = 0	5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2.5A			5.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 2.5A			1.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 1500V; R <sub>BE</sub> = 0			500	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 5V	5		25	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 10A; V <sub>CE</sub> = 5V	4		7	
t <sub>f</sub>	Fall Time	I <sub>CP</sub> = 7A, I <sub>B1</sub> = 2.4A; f <sub>H</sub> = 31.5kHz			0.4	μ s